SQJ886EP

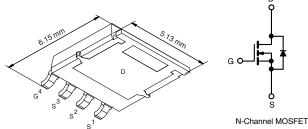


Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0045
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0055
I _D (A)	60
Configuration	Single

PowerPAK[®] SO-8L Single



FEATURES

- TrenchFET[®] Power MOSFET
- AEC-Q101 Qualified^c
- 100 % R_g and UIS Tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ886EP-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C		60		
Continuous Drain Current	T _C = 125 °C	I _D	45		
Continuous Source Current (Diode Conduction)		I _S	50	А	
Pulsed Drain Current ^a		I _{DM}	240		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	36		
Single Pulse Avalanche Energy	L = 0.1 MH	E _{AS}	64	mJ	
Marian Maria Diasia ati a si	$T_{\rm C} = 25 ^{\circ}{\rm C}$	P	55	14/	
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	18	W	
Operating Junction and Storage Temperatu	re Range	T _J , T _{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temper	ature) ^{d, e}		260	-0	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R _{thJA}	70	°C/W
Junction-to-Case (Drain)		R _{thJC}	2.7	C/W

Notes

b. When mounted on 1" square PCB (FR-4 material).

c. Parametric verification ongoing.

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

1

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

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PARAMETER	SYMBOL	TES	ST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							•
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	40	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2.0	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} =	: 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	А
		$V_{GS} = 10 V$	I _D = 15.3 A	-	0.0036	0.0045	Ω
Drain-Source On-State Resistance ^a	В	$V_{GS} = 4.5 V$	I _D = 13.8 A	-	0.0045	0.0055	
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 15.3 A, T _J = 125 °C	-	-	0.0072	
		V _{GS} = 10 V	I _D = 15.3 A, T _J = 175 °C	-	-	0.0088	
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 15.3 A		-	105	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		V _{DS} = 20 V, f = 1 MHz	-	2338	2922	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	356	445	
Reverse Transfer Capacitance	C _{rss}			-	147	184	
Total Gate Charge ^c	Qg			-	43	65	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	8	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	7	-	
Gate Resistance	Rg	f = 1 MHz		1.25	2.45	5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	8	12	
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 2 \Omega$ $I_{D} \cong 10 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	17	25	- ns
Turn-Off Delay Time ^c	t _{d(off)}			-	29	44	
Fall Time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Char	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	240	А
Forward Voltage	V _{SD}	I _F =	: 10.1 A, V _{GS} = 0	-	0.8	1.2	V

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

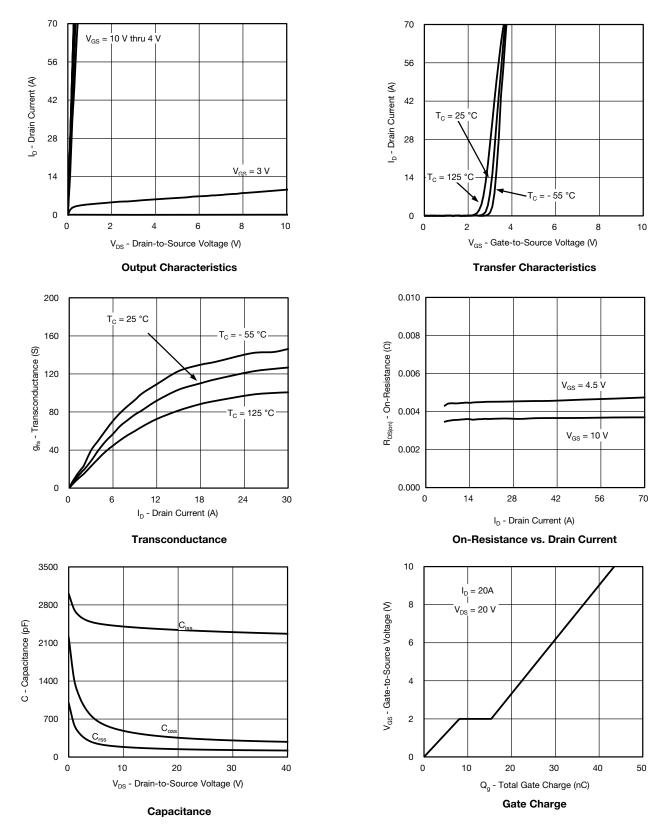
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



3

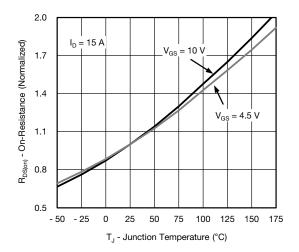
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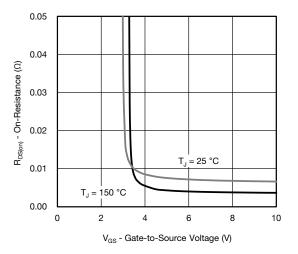
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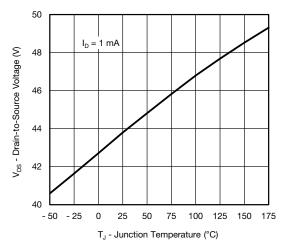
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



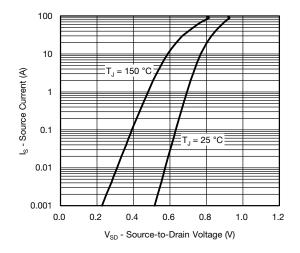
On-Resistance vs. Junction Temperature



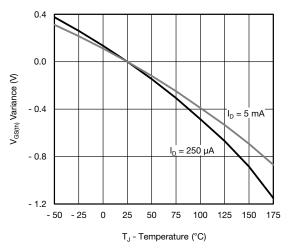
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



Threshold Voltage

S12-3129-Rev. A, 07-Jan-13

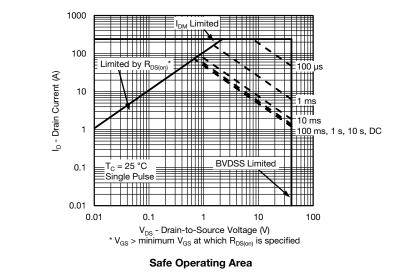
4

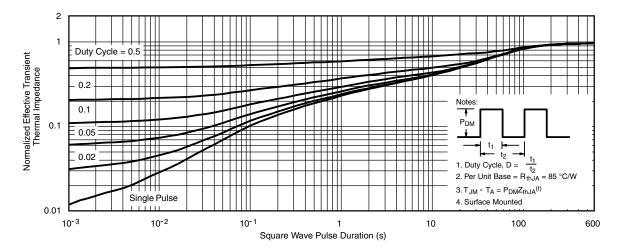
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

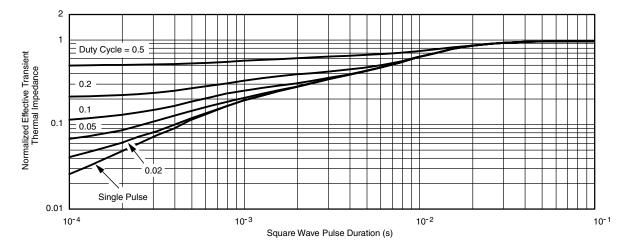




Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62790.



PowerPAK[®] SO-8L

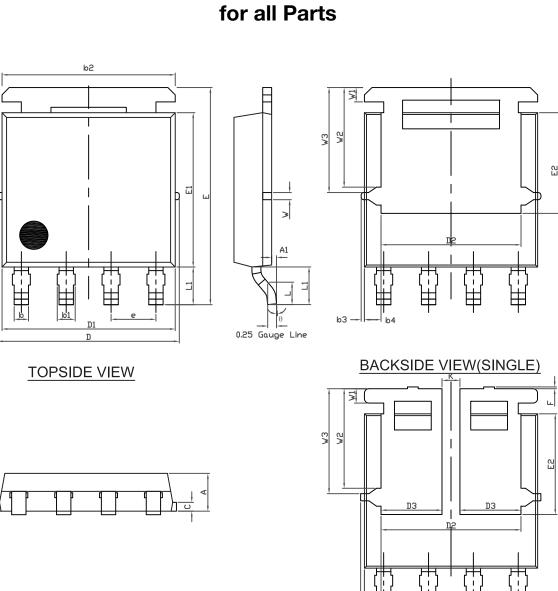
Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK SO-8L package:

DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE	
SQJ200EP		SQJ200EP-T1_GE3	
SQJ202EP	-	SQJ202EP-T1_GE3	
SQJ401EP	SQJ401EP-T1-GE3	SQJ401EP-T1_GE3	
SQJ402EP	SQJ402EP-T1-GE3	SQJ402EP-T1_GE3	
SQJ403EEP	SQJ403EEP-T1-GE3	SQJ403EEP-T1_GE3	
SQJ403EP	-	SQJ403EP-T1_GE3	
SQJ410EP	SQJ410EP-T1-GE3	SQJ410EP-T1_GE3	
SQJ412EP	SQJ412EP-T1-GE3	SQJ412EP-T1_GE3	
SQJ422EP	SQJ422EP-T1-GE3	SQJ422EP-T1_GE3	
SQJ431EP	SQJ431EP-T1-GE3	SQJ431EP-T1_GE3	
SQJ443EP	SQJ443EP-T1-GE3	SQJ443EP-T1_GE3	
SQJ446EP	-	SQJ446EP-T1_GE3	
SQJ456EP	SQJ456EP-T1-GE3	SQJ456EP-T1_GE3	
SQJ459EP	-	SQJ459EP-T1_GE3	
SQJ460AEP	-	SQJ460AEP-T1_GE3	
SQJ461EP	SQJ461EP-T1-GE3	SQJ461EP-T1_GE3	
SQJ463EP	SQJ463EP-T1-GE3	SQJ463EP-T1_GE3	
SQJ465EP	SQJ465EP-T1-GE3	SQJ465EP-T1_GE3	
SQJ469EP	SQJ469EP-T1-GE3	SQJ469EP-T1_GE3	
SQJ486EP	SQJ486EP-T1-GE3	SQJ486EP-T1_GE3	
SQJ488EP	SQJ488EP-T1-GE3	SQJ488EP-T1_GE3	
SQJ500AEP	SQJ500AEP-T1-GE3	SQJ500AEP-T1_GE3	
SQJ840EP	SQJ840EP-T1-GE3	SQJ840EP-T1_GE3	
SQJ844AEP	SQJ844AEP-T1-GE3	SQJ844AEP-T1_GE3	
SQJ850EP	SQJ850EP-T1-GE3	SQJ850EP-T1_GE3	
SQJ858AEP	SQJ858AEP-T1-GE3	SQJ858AEP-T1_GE3	
SQJ886EP	SQJ886EP-T1-GE3	SQJ886EP-T1_GE3	
SQJ910AEP	SQJ910AEP-T1-GE3	SQJ910AEP-T1_GE3	
SQJ912AEP	SQJ912AEP-T1-GE3	SQJ912AEP-T1_GE3	
SQJ940EP	SQJ940EP-T1-GE3	SQJ940EP-T1_GE3	
SQJ942EP	SQJ942EP-T1-GE3	SQJ942EP-T1_GE3	
SQJ951EP	SQJ951EP-T1-GE3	SQJ951EP-T1_GE3	
SQJ952EP	-	SQJ952EP-T1_GE3	
SQJ956EP	SQJ956EP-T1-GE3	SQJ956EP-T1_GE3	
SQJ960EP	SQJ960EP-T1-GE3	SQJ960EP-T1_GE3	
SQJ963EP	SQJ963EP-T1-GE3	SQJ963EP-T1_GE3	
SQJ968EP	SQJ968EP-T1-GE3	SQJ968EP-T1_GE3	
SQJ980AEP	SQJ980AEP-T1-GE3	SQJ980AEP-T1_GE3	
SQJ992EP	SQJ992EP-T1-GE3	SQJ992EP-T1_GE3	

Note

a. Old ordering code is obsolete and no longer valid for new orders





PowerPAK[®] SO-8L Case Outline

Revision: 07-Sep-15

1

b3

BACKSIDE VIEW(DUAL)

Package Information



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DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	•		0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC	•	0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W		0.23			0.009		
W1		0.41			0.016		
W2	2.82			0.111			
W3		2.96		0.117			
q	0°	-	10°	0°	-	10°	

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



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